Preferred Device

Sensitive Gate Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed for industrial and consumer applications such as temperature, light and speed control; process and remote controls; warning systems; capacitive discharge circuits and MPU interface.

Features

- Center Gate Geometry for Uniform Current Density
- All Diffused and Glass-Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Low Trigger Currents, 200 μA Maximum for Direct Driving from Integrated Circuits
- Pb-Free Packages are Available*

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
$\begin{tabular}{lll} Peak Repetitive Off-State Voltage (Note 1) \\ (T_J = -40 to 110 ^{\circ}C, Sine Wave, \\ 50 Hz to 60 Hz) & MCR72-3 \\ MCR72-6 \\ MCR72-8 \\ \end{tabular}$	V _{DRM,} V _{RRM}	100 400 600	٧
On-State RMS Current (180° Conduction Angles; T _C = 83°C)	I _{T(RMS)}	8.0	Α
Peak Non-Repetitive Surge Current (1/2 Cycle, 60 Hz, T _J = 110°C)	I _{TSM}	100	Α
Circuit Fusing Considerations (t = 8.3 ms)	l ² t	40	A ² s
Forward Peak Gate Voltage (t ≤ 10 μs, T _C = 83°C)	V _{GM}	±5.0	٧
Forward Peak Gate Current (t \leq 10 μ s, T _C = 83°C)	I _{GM}	1.0	Α
Forward Peak Gate Power (t ≤ 10 μs, T _C = 83°C)	P _{GM}	5.0	W
Average Gate Power (t = 8.3 ms, T _C = 83°C)	P _{G(AV)}	0.75	W
Operating Junction Temperature Range	TJ	-40 to +110	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C
Mounting Torque	_	8.0	in. lb.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking

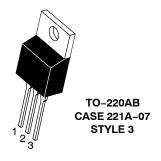


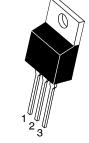
ON Semiconductor®

http://onsemi.com

SCRs 8 AMPERES RMS 100 thru 600 VOLTS







TO-220AB
CASE 221A-09
STYLE 3

PIN ASSIGNMENT			
1 Cathode			
2	Anode		
3	Gate		
4	Anode		

MARKING AND ORDERING INFORMATION

See detailed marking, ordering, and shipping information in the package dimensions section on page 5 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	2.2	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	60	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Secs	TL	260	°C

FLECTRICAL CHARACTERISTICS (To = 25°C unless otherwise noted.)

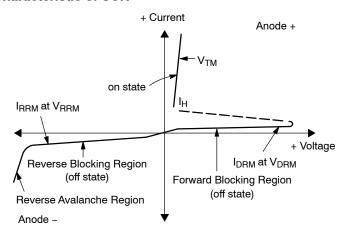
Characteristic			Тур	Max	Unit
	•	•	•		
T _J = 25°C T _J = 110°C	I _{DRM} , I _{RRM}	_ _	- -	10 500	μ Α μ Α
	I _{CCH}	4	4	μА	μΑ
	•				
	V _{TM}	-	1.7	2.0	V
	I _{GT}	-	30	200	μΑ
Gate Trigger Voltage (Continuous dc) (Note 3) $(V_D = 12 \text{ V}, \text{ R}_L = 100 \Omega)$		-	0.5	1.5	V
Gate Non–Trigger Voltage (V_D = 12 Vdc, R_L = 100 Ω , T_J = 110°C)		0.1	-	-	V
	lн	-	-	6.0	mA
Gate Controlled Turn-On Time (V_D = Rated V_{DRM} , I_{TM} = 16 A, I_G = 2 mA)			1.0	-	μs
veform)	dv/dt	-	10	-	V/μs
	T _J = 110°C	$T_{J} = 25^{\circ}C$ $T_{J} = 110^{\circ}C$ I_{CCH} V_{TM} I_{GT} V_{GD} I_{H} t_{gt} dv/dt	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

^{2.} Ratings apply for negative gate voltage or R_{GK} = 1 kΩ. Devices shall not have a positive gate voltage concurrently with a negative voltage on the anode. Devices should not be tested with a constant current source for forward and reverse blocking capability such that the voltage applied exceeds the rated blocking voltage.

3. R_{GK} current not included in measurement.

Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Off State Forward Voltage
I _{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Off State Reverse Voltage
I _{RRM}	Peak Reverse Blocking Current
V_{TM}	Peak On State Voltage
I _H	Holding Current



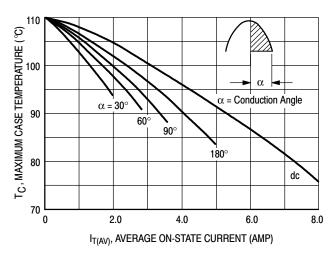


Figure 1. Average Current Derating

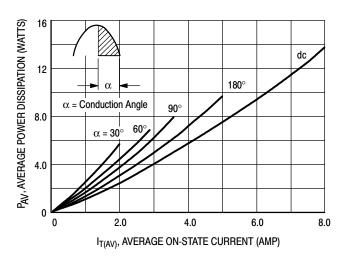


Figure 2. On-State Power Dissipation

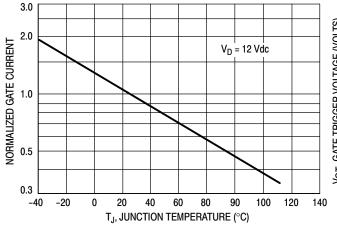


Figure 3. Normalized Gate Current

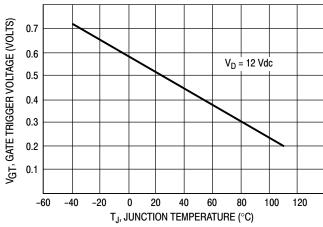


Figure 4. Gate Voltage

MARKING DIAGRAMS

TO-220AB CASE 221A-07

AY WW MCR72-xG AKA

A = Assembly Location

Y = Year WW = Work Week MCR72-x = Device Code

x = 3, 6, 8, or 8T G = Pb-Free Package AKA = Diode Polarity

TO-220AB CASE 221A-09



A = Assembly Location

Y = Year

WW = Work Week

MCR72-6T = Device Code

G = Pb-Free Package

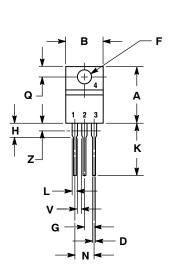
AKA = Diode Polarity

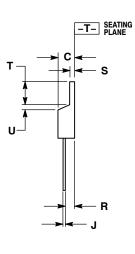
ORDERING INFORMATION

Device	Package	Shipping
MCR72-3	TO-220AB	
MCR72-3G	TO-220AB (Pb-Free)	FOO Halla (P.
MCR72-6	TO-220AB	500 Units / Box
MCR72-6G	TO-220AB (Pb-Free)	
MCR72-6T	TO-220AB	
MCR72-6TG	TO-220AB (Pb-Free)	50 Units / Rail
MCR72-8	TO-220AB	
MCR72-8G	TO-220AB (Pb-Free)	500 Units / Box
MCR72-8T	TO-220AB	
MCR72-8TG	TO-220AB (Pb-Free)	50 Units / Rail

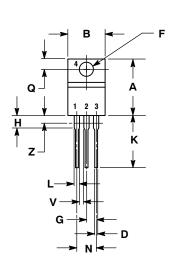
PACKAGE DIMENSIONS

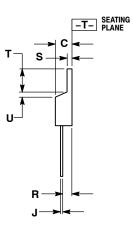
TO-220 CASE 221A-07 **ISSUE 0**





TO-220 CASE 221A-09 **ISSUE AF**





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

- STYLE 3: PIN 1. CATHODE
 - 2. ANODE 3. GATE

 - ANODE

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- STYLE 3:
 PIN 1. CATHODE
 2. ANODE
 3. GATE

 - GATE
 ANODE

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